

ABSTRACT OF THE DISCLOSURE

An active layer (14) which has a gate electrode (11), a gate insulating film (12), a source (14s) and a drain (14d) is formed on an insulating substrate (10), so that a thin film transistor is formed. On this, an inter-layer insulating film (15) and a flattening insulating film (17) are laminated. Subsequently, after a contact hole is formed in the inter-layer insulating film (15) and the flattening insulating film (17), a back-surface electrode (41) constituted of molybdenum or another high melting point metal is formed, on which a display electrode (18) constituted of aluminum is formed. The presence of the back-surface electrode (41) prevents protrusions from being generated on the display electrode (18).

DRAFT - 554732-10